

Vishay Siliconix

Low-Leakage Pico-Amp Diodes

PAD1	JPAD5	SSTPAD5			
PAD5	JPAD50	SSTPAD100			
PAD50					

PRODUCT SUMMARY					
Part Number	I _R Max (pA)				
PAD1	-1				
PAD5/JPAD5/SSTPAD5	-5				
PAD50/JPAD50	-50				
SSTPAD100	-100				

FEATURES

- Ultralow Leakage: PAD1 <1 pA
- Ultralow Capacitance: PAD1 <0.8 pF
- Two-Leaded Package

BENEFITS

- Negligible Circuit Leakage Contribution
- Circuit "Transparent" Except to Shunt High-Frequency Spikes
- Simplicity of Operation

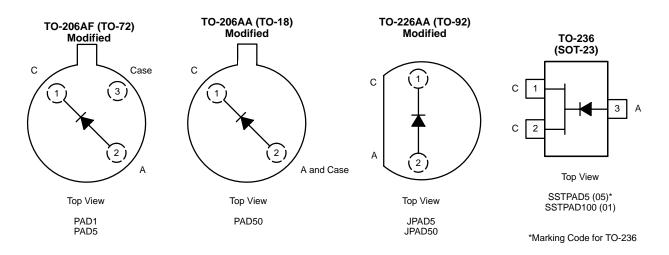
APPLICATIONS

- Op Amp Input Protection
- Multiplexer Overvoltage Protection

DESCRIPTION

The PAD/JPAD/SSTPAD series of extremely low-leakage diodes provides a superior alternative to conventional diode technology when reverse current (leakage) must be minimized. They feature leakage currents ranging from -1 pA (PAD1) to -100 pA (SSTPAD100) to support a wide range of applications. These devices are well suited for use in applications such as input protection for operational amplifiers.

The hermetically sealed TO-206AF (TO-72) package allows full military processing per MIL-S-19500 (see Military Information). The TO-226A (TO-92) plastic package provides a low-cost option. The TO-236 (SOT-23) package provides surface-mount capability. Both J and SST series are available in tape-and-reel for automated assembly. (See Packaging Information.)



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ABSOLUTE MAXIMUM RATINGS^a

Forward Current:	(PAD 50 mA
Total Device Dissipation:	(JPAD/SSTPAD) 10 mA (PAD) ^b 300 mW
	(JPAD/SSTPAD) ^b
Operation Junction Temp:	
	(JPAD/SSTPAD) ^c –55 to 150°C
Lead Temperature (1/16" from	m case for 10 sec.) 300°C

Notes:

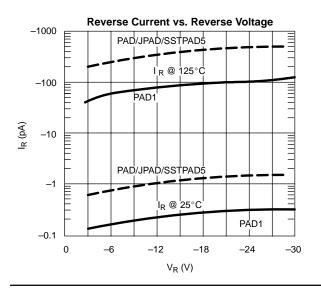
- $T_A = 25^{\circ}$ C unless otherwise noted. Derate 2 mW/°C above 25°C. Derate 2.8 mW/°C above 25°C. a.
- b.
- c.

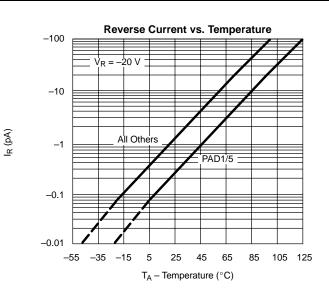
SPECIFICATIONS SPECIFICATIONS (T _A = 25° C UNLESS OTHERWISE NOTED)									
		Test Conditions		Limits					
Parameter	Symbol			Min	Typ ^a	Мах	Unit		
Static									
Reverse Current		V _R = -20 V	PAD1		-0.3	-1	рА		
	I _R		PAD5/JPAD5/SSTPAD5		-1	-5			
			PAD50/JPAD50		-5	-50			
			SSTPAD100		-10	-100			
Reverse Breakdown Voltage	BV _R	I _R = −1 μA	PAD1/PAD5	-45	-60		- V		
			SSTPAD5/100	-30	-55				
			All Others	-35	-55				
Forward Voltage Drop	V _F	I _F = 1 mA			0.8	1.5	1		
Dynamic									
Reverse Capacitance	C _R	V _R = -5V, f = 1 MHz	PAD1/PAD5		0.5	0.8	pF		
			All Others		1.5	2			

Notes:

a. Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing.

TYPICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ UNLESS OTHERWISE NOTED)







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